

**METHOD FOR PREPARING A BONDING SURFACE OF A
SEMICONDUCTOR LAYER OF A WAFER**

ABSTRACT

A method for preparing a bonding surface of a semiconductor layer of a wafer is described. The method includes treating the bonding surface to oxidize contaminants, and then cleaning the bonding surface to remove essentially all remaining contaminants. Ozone is then used to oxidize the bonding surface to improve the hydrophilic properties of the bonding surface. In an implementation, two wafers are prepared and then bonded together to form a structure.